



CEPF630/CEBF630

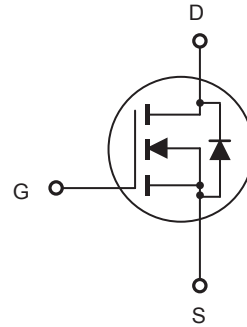
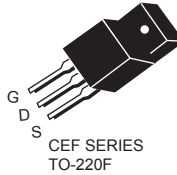
CEFF630

N-Channel Enhancement Mode Field Effect Transistor

FEATURES

| Type | V _{DSS} | R _{DS(ON)} | I _D | @V _{GS} |
|---------|------------------|---------------------|------------------|------------------|
| CEPF630 | 200V | 0.35Ω | 10A | 10V |
| CEBF630 | 200V | 0.35Ω | 10A | 10V |
| CEFF630 | 200V | 0.35Ω | 10A ^d | 10V |

- Super high dense cell design for extremely low R_{DS(ON)}.
- High power and current handling capability.
- Lead free product is acquired.



ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$ unless otherwise noted

| Parameter | Symbol | Limit | | Units |
|--|-----------------------------------|------------|-----------------|-------|
| | | TO-220/263 | TO-220F | |
| Drain-Source Voltage | V _{DS} | 200 | | V |
| Gate-Source Voltage | V _{GS} | ±20 | | V |
| Drain Current-Continuous | I _D | 10 | 10 ^d | A |
| Drain Current-Pulsed ^a | I _{DM} ^e | 40 | 40 ^d | A |
| Maximum Power Dissipation @ T _C = 25°C - Derate above 25°C | P _D | 75 | 33 | W |
| | | 0.6 | 0.27 | W/°C |
| Operating and Store Temperature Range | T _J , T _{stg} | -55 to 150 | | °C |

Thermal Characteristics

| Parameter | Symbol | Limit | | Units |
|---|------------------|-------|-----|-------|
| Thermal Resistance, Junction-to-Case | R _{θJC} | 1.5 | 3.7 | °C/W |
| Thermal Resistance, Junction-to-Ambient | R _{θJA} | 62.5 | 65 | °C/W |



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Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

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| Parameter | Symbol | Test Condition | Min | Typ | Max | Units |
|--|--------------|---|-----|------|------|------------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS} = 0V, I_D = 250\mu A$ | 200 | | | V |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = 160V, V_{GS} = 0V$ | | | 25 | μA |
| Gate Body Leakage Current, Forward | I_{GSSF} | $V_{GS} = 20V, V_{DS} = 0V$ | | | 100 | nA |
| Gate Body Leakage Current, Reverse | I_{GSSR} | $V_{GS} = -20V, V_{DS} = 0V$ | | | -100 | nA |
| On Characteristics^b | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{GS} = V_{DS}, I_D = 250\mu A$ | 2 | | 4 | V |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 5A$ | | | 350 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS} = 10V, I_D = 5A$ | | 6 | | S |
| Dynamic Characteristics^c | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS} = 25V, V_{GS} = 0V, f = 1.0\text{ MHz}$ | | 680 | | pF |
| Output Capacitance | C_{oss} | | | 105 | | pF |
| Reverse Transfer Capacitance | C_{rss} | | | 40 | | pF |
| Switching Characteristics^c | | | | | | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD} = 100V, I_D = 5A, V_{GS} = 10V, R_{GEN} = 50\Omega$ | | 50 | 100 | ns |
| Turn-On Rise Time | t_r | | | 80 | 160 | ns |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 55 | 110 | ns |
| Turn-Off Fall Time | t_f | | | 40 | 80 | ns |
| Total Gate Charge | Q_g | $V_{DS} = 160V, I_D = 5.9A, V_{GS} = 10V$ | | 27 | 54 | nC |
| Gate-Source Charge | Q_{gs} | | | 4 | | nC |
| Gate-Drain Charge | Q_{gd} | | | 14.7 | | nC |
| Drain-Source Diode Characteristics and Maximum Ratings | | | | | | |
| Drain-Source Diode Forward Current | I_S | | | | 10 | A |
| Drain-Source Diode Forward Voltage ^b | V_{SD} | $V_{GS} = 0V, I_S = 10A$ | | | 1.5 | V |
| Notes : <input type="checkbox"/> a.Repetitive Rating : Pulse width limited by maximum junction temperature . b.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$. <input type="checkbox"/> c.Guaranteed by design, not subject to production testing. <input type="checkbox"/> d.Limited only by maximum temperature allowed . e.Pulse width limited by safe operating area . f.Full package $I_{S(max)} = 6.4A$. g.Full package V_{SD} test condition $I_S = 6.4A$. | | | | | | |



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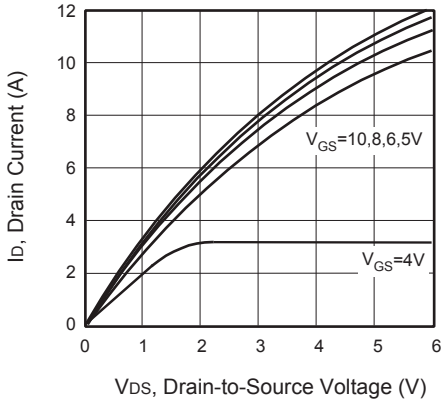


Figure 1. Output Characteristics

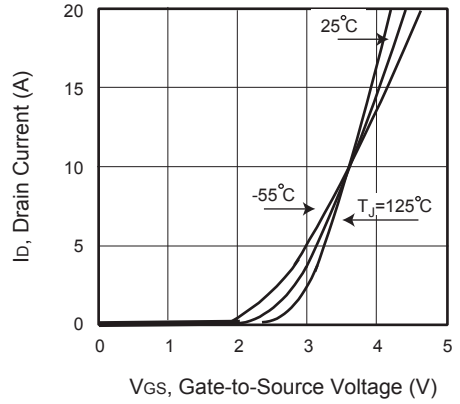


Figure 2. Transfer Characteristics

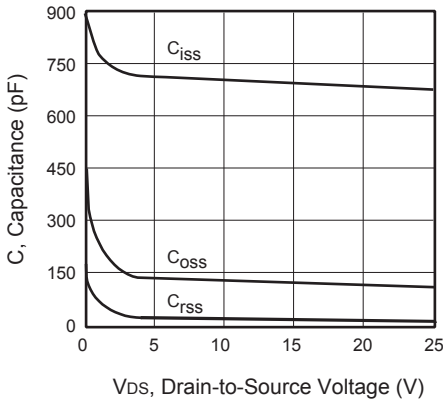


Figure 3. Capacitance

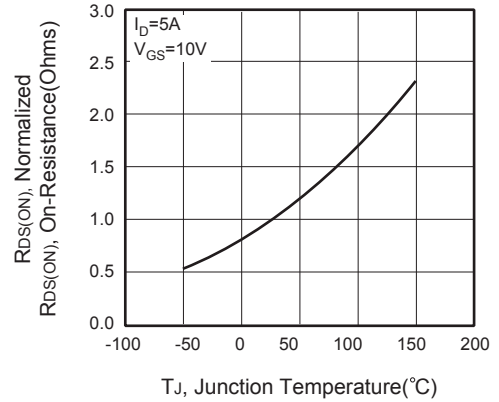


Figure 4. On-Resistance Variation with Temperature



Figure 5. Gate Threshold Variation with Temperature

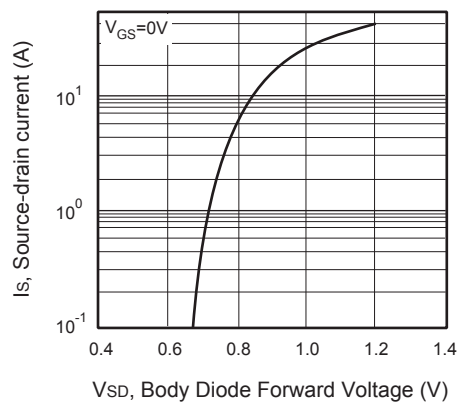


Figure 6. Body Diode Forward Voltage Variation with Source Current



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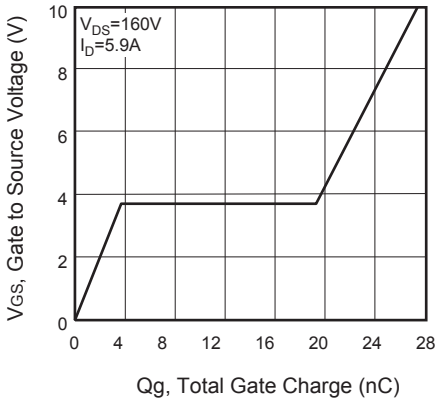


Figure 7. Gate Charge

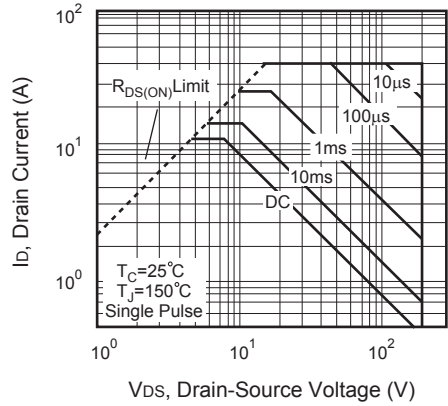


Figure 8. Maximum Safe Operating Area

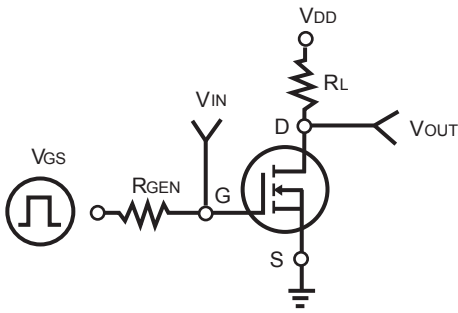


Figure 9. Switching Test Circuit

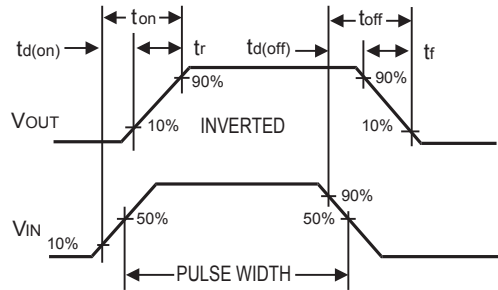


Figure 10. Switching Waveforms

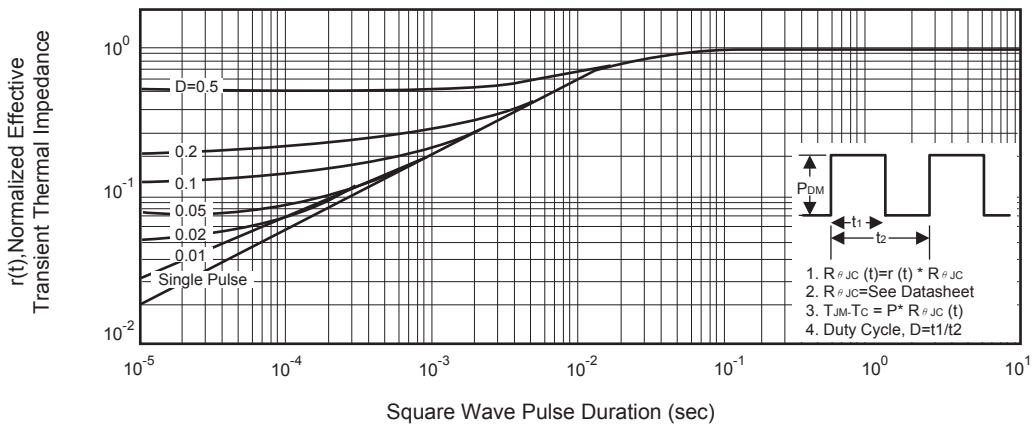


Figure 11. Normalized Thermal Transient Impedance Curve